400 Watt Peak Power Zener Transient Voltage Suppressors

Unidirectional

The SMA series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMA series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable SURMETIC® package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Features

- Working Peak Reverse Voltage Range 5.0 V to 78 V
- Standard Zener Breakdown Voltage Range 6.7 V to 91.25 V
- Peak Power 400 W @ 1 ms
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Response Time is Typically < 1 ns
- Flat Handling Surface for Accurate Placement
- Package Design for Top Slide or Bottom Circuit Board Mounting
- Low Profile Package
- AEC-Q101 Qualified and PPAP Capable
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- Pb–Free Packages are Available*

Mechanical Characteristics:

CASE: Void-free, transfer-molded plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

POLARITY: Cathode indicated by molded polarity notch or polarity

MOUNTING POSITION: Any



ON Semiconductor®

http://onsemi.com

PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS 5.0 - 78 V, 400 W PEAK POWER



SMA CASE 403D STYLE 1



MARKING DIAGRAM



= Device Code (Refer to page 3)

= Assembly Location

= Year

= Work Week = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
1SMAxxAT3	SMA	5,000 / Tape & Reel
1SMAxxAT3G	SMA (Pb-Free)	5,000 / Tape & Reel
SZ1SMAxxAT3G	SMA (Pb-Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

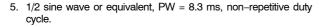
Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T _L = 25°C, Pulse Width = 1 ms	P _{PK}	400	W
DC Power Dissipation @ T _L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction to Lead	P _D R _{θJL}	1.5 20 50	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T _A = 25°C Derate Above 25°C Thermal Resistance from Junction to Ambient	P_{D} $R_{ hetaJA}$	0.5 4.0 250	W mW/°C °C/W
Forward Surge Current (Note 4) @ T _A = 25°C	I _{FSM}	40	Α
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

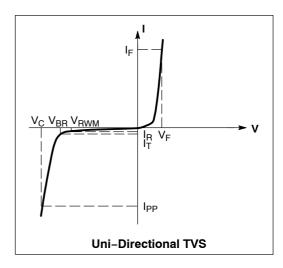
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 10 X 1000 μs, non-repetitive.
- 2. 1" square copper pad, FR-4 board.
- 3. FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403B case outline dimensions spec.
- 4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 3.5 \text{ V Max.}$ @ $I_F = 30 \text{ A for all types}$) (Note 5)

Symbol	Parameter			
I _{PP}	Maximum Reverse Peak Pulse Current			
V _C	Clamping Voltage @ I _{PP}			
V _{RWM}	Working Peak Reverse Voltage			
I _R	Maximum Reverse Leakage Current @ V _{RWM}			
V _{BR}	Breakdown Voltage @ I _T			
I _T	Test Current			
l _F	Forward Current			
V _F	Forward Voltage @ I _F			





ELECTRICAL CHARACTERISTICS

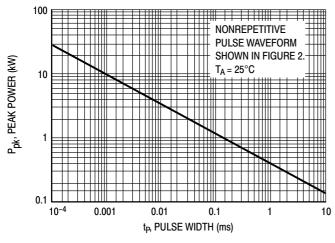
		V _{RWM}	M IR@	Breakdown Voltage			V _C @ I _{PP} (Note 8)		С Тур.	
	Device	(Note 6)	V _{RWM}	V _{BR} (Volts) (Note 7) @ I _T		@ I _T	V _C I _{PP}		(Note 9)	
Device	Marking	Volts	μΑ	Min	Nom	Max	mA	Volts	Amps	pF
1SMA5.0AT3, G	QE	5.0	400	6.4	6.7	7.0	10	9.2	43.5	2035
1SMA6.0AT3, G	QG	6.0	400	6.67	7.02	7.37	10	10.3	38.8	1730
1SMA6.5AT3, G	QK	6.5	250	7.22	7.6	7.98	10	11.2	35.7	1605
1SMA7.0AT3, G	QM	7.0	250	7.78	8.19	8.6	10	12.0	33.3	1505
1SMA7.5AT3, G	QP	7.5	50	8.33	8.77	9.21	1	12.9	31.0	1415
1SMA8.0AT3, G	QR	8.0	25	8.89	9.36	9.83	1	13.6	29.4	1035
1SMA8.5AT3, G	QT	8.5	5.0	9.44	9.92	10.4	1	14.4	27.8	1265
1SMA9.0AT3, G	QV	9.0	2.5	10	10.55	11.1	1	15.4	26.0	1200
1SMA10AT3, G	QX	10	2.5	11.1	11.7	12.3	1	17.0	23.5	1090
1SMA11AT3, G	QZ	11	2.5	12.2	12.85	13.5	1	18.2	22.0	1000
1SMA12AT3, G	RE	12	2.5	13.3	14.0	14.7	1	19.9	20.1	925
1SMA13AT3, G	RG	13	2.5	14.4	15.15	15.9	1	21.5	18.6	860
1SMA14AT3, G	RH	14	2.5	15.6	16.4	17.2	1	23.2	17.2	800
1SMA15AT3, G	RM	15	2.5	16.7	17.6	18.5	1	24.4	16.4	758
SZ/1SMA16AT3, G	RP	16	2.5	17.8	18.75	19.7	1	26.0	15.4	715
1SMA17AT3, G	RR	17	2.5	18.9	19.9	20.9	1	27.6	14.5	680
1SMA18AT3, G	RT	18	2.5	20	21.05	22.1	1	29.2	13.7	645
SZ/1SMA20AT3, G	RV	20	2.5	22.2	23.35	24.5	1	32.4	12.3	585
1SMA22AT3, G	RX	22	2.5	24.4	25.65	26.9	1	35.5	11.3	540
SZ/1SMA24AT3, G	RZ	24	2.5	26.7	28.1	29.5	1	38.9	10.3	500
SZ/1SMA26AT3, G	SE	26	2.5	28.9	30.4	31.9	1	42.1	9.5	460
SZ/1SMA28AT3, G	SG	28	2.5	31.1	32.75	34.4	1	45.4	8.8	430
SZ/1SMA30AT3, G	SK	30	2.5	33.3	35.05	36.8	1	48.4	8.3	405
SZ/1SMA33AT3, G	SM	33	2.5	36.7	38.65	40.6	1	53.3	7.5	375
SZ/1SMA36AT3, G	SP	36	2.5	40	42.1	44.2	1	58.1	6.9	345
1SMA40AT3, G	SR	40	2.5	44.4	46.75	49.1	1	64.5	6.2	315
SZ/1SMA43AT3, G	ST	43	2.5	47.8	50.3	52.8	1	69.4	5.8	295
1SMA45AT3, G	SV	45	2.5	50	52.65	55.3	1	72.2	5.5	280
1SMA48AT3, G	SX	48	2.5	53.3	56.1	58.9	1	77.4	5.2	265
1SMA51AT3, G	SZ	51	2.5	56.7	59.7	62.7	1	82.4	4.9	250
1SMA54AT3, G	TE	54	2.5	60	63.15	66.3	1	87.1	4.6	240
1SMA58AT3, G	TG	58	2.5	64.4	67.8	71.5	1	93.6	4.3	225
1SMA64AT3, G	TM	64	2.5	71.1	74.85	78.6	1	103	3.9	205
SZ/1SMA70AT3, G	TP	70	2.5	77.8	81.9	86.0	1	113	3.5	190
1SMA75AT3, G	TR	75	2.5	83.3	87.7	92.1	1	121	3.3	180

A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
 V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
 Surge current waveform per Figure 2 and derate per Figure 3.
 Bias voltage = 0 V, F = 1.0 MHz, T_J = 25°C.

[†]Please see 1SMA10CAT3 to 1SMA75CAT3 for Bidirectional devices.

^{*}The "G" suffix indicates Pb-Free package available.

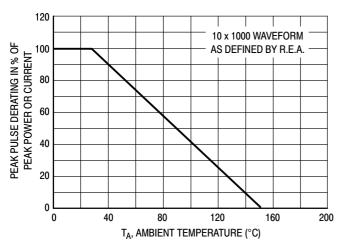
RATING AND TYPICAL CHARACTERISTIC CURVES



120 $T_A = 25^{\circ}C$ ≤ 10 μs PW (ID) IS DEFINED AS THE lppm, PEAK PULSE CURRENT (%) 100 POINT WHERE THE PEAK CURRENT DECAYS TO 50% OF Ipp. PEAK VALUE -80 Ippm 60 HALF VALUE - Ipp/2 40 10/1000 μs WAVEFORM AS DEFINED BY R.E.A. 20 0 0 2 t, TIME (ms)

Figure 1. Pulse Rating Curve

Figure 2. Pulse Waveform



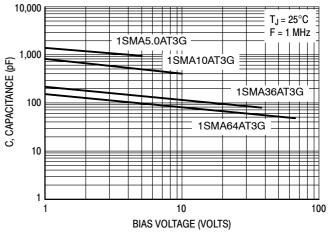


Figure 3. Pulse Derating Curve

Figure 4. Typical Junction Capacitance vs.
Bias Voltage

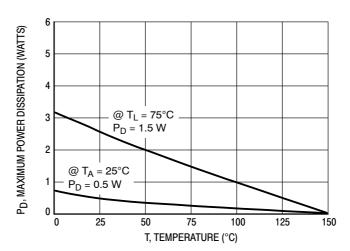
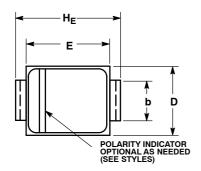


Figure 5. Steady State Power Derating

PACKAGE DIMENSIONS

SMA CASE 403D-02 ISSUE F



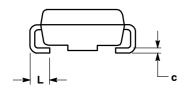
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 403D-01 OBSOLETE, NEW STANDARD IS 403D-02.

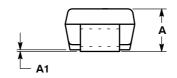
	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.97	2.10	2.20	0.078	0.083	0.087	
A1	0.05	0.10	0.15	0.002	0.004	0.006	
b	1.27	1.45	1.63	0.050	0.057	0.064	
С	0.15	0.28	0.41	0.006	0.011	0.016	
D	2.29	2.60	2.92	0.090	0.103	0.115	
E	4.06	4.32	4.57	0.160	0.170	0.180	
HE	4.83	5.21	5.59	0.190	0.205	0.220	
L	0.76	1.14	1.52	0.030	0.045	0.060	



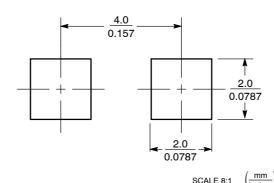
PIN 1. CATHODE (POLARITY BAND)

2. ANODE





SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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